(translation)

AMENDMENT

(Amended under PCT Article 34)

To Mr. Seiji HAMADA , Commissioner of the Japan Patent Office

1. Identification of the International Application:
   PCT/ JP03/02408

2. Applicant :

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4. Subject of Amendment :
   Specification and Claims

5. Content of Amendment :
   As in the attached document

6. Item of Attached Document(s) :
   (1) Page 2 and 2/1 of Specification (Page number 4 and 5 as in the attached document)
   (2) Page 15 of Claims (Page number 30-32 as in the attached document)

Content of amendment

(1) The description "the second conductivity type semiconductor layer being in contact with the front electrode" (see page 2, line 17 of the specification) is amended to the description "the second conductivity type semiconductor layer being at its partial area contact with the front electrode"

(2) The description "the steps (b) of implanting second conductivity type impurities into the semiconductor substrate through the film to form a second conductivity type semiconductor layer on the surface of the semiconductor substrate." (see page 2, lines 21-22 of the specification) is amended to the description "the steps (b) of implanting second conductivity type impurities into the semiconductor substrate through the film to form a second conductivity type semiconductor layer on the surface of the semiconductor substrate, and step (c) of forming a front electrode that is in contact with the convex portion which constitute a part of the semiconductor substrate surface."

(3) The description "steps (b') of implanting second conductivity type impurities into the semiconductor substrate from the film to form a second conductivity type semiconductor layer on the surface of the semiconductor substrate." (see page 2, lines 25-26 of the specification) is amended to the description "steps (b') of implanting second conductivity type impurities into the semiconductor substrate from the film to form a second conductivity type semiconductor layer on the surface of the semiconductor substrate, and steps (c') of forming a front electrode that is in contact with the concave portion which constitute a part of the semiconductor substrate surface."

(4) The description "the second conductivity type semiconductor layer being in contact with the front electrode" (see page 15 of claim 1) is amended to the description "the second conductivity type semiconductor layer being at its partial area contact with the front electrode"

(5) The description "(b) implanting second conductivity type impurities into the semiconductor substrate through the film to form a second conductivity type semiconductor layer on the surface of the semiconductor substrate." (see page 15 of claim 6) is amended to the description "(b) implanting second conductivity type impurities into the semiconductor substrate through the film to form a second conductivity type semiconductor layer on the surface of the semiconductor substrate; and (c) forming a front electrode that is in contact with the convex portion which constitute a part of the semiconductor substrate surface." and claim 7 is canceled.

(6) The description "(a) forming a film containing second conductivity type impurities on a semiconductor substrate having convex and concave portions formed on its surface in such a manner that the film becomes thicker from the convex portions to the concave portions; and (b) implanting second conductivity type impurities into the semiconductor substrate from the film to form a second conductivity type semiconductor layer on the surface of the semiconductor substrate." (see page 15 of claim 8) is amended to the description "(a') forming a film containing second conductivity type impurities on a semiconductor substrate having convex and concave portions formed on its surface in such a manner that the film becomes thicker from the convex portion to the concave portion; and (b') implanting second conductivity type impurities into the semiconductor substrate from the film to form a second conductivity type semiconductor layer on the surface of the semiconductor substrate; and (c') forming a front electrode that is in contact with the concave portion which constitute a part of the semiconductor substrate surface." and claim 9 is canceled.